



#### 50V NPN LOW SATURATION SWITCHING TRANSISTOR

#### **Features**

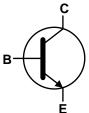
- $BV_{CEO} > 50V$
- I<sub>C</sub> = 3A Continuous Collector Current
- I<sub>CM</sub> = 6A Peak Pulse Current
- $R_{CE(SAT)}$  = 75m $\Omega$  for a Low Equivalent On-Resistance
- Low Saturation Voltage (200mV Max @ 1A)
- hFE Characterized up to 6A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

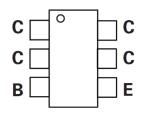
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.015 grams (Approximate)



Top View



Device Symbol



Top View Pin-Out

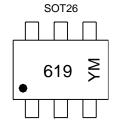
#### **Ordering Information** (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXT10N50DE6TA	AEC-Q101	619	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>
  4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



619 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Kev

 Bate Code	1103												
Year	201	5	2016	2017	2018	2019	2020	202	1 20	22 2	2023	2024	2025
Code	С		D	E	F	G	Н		,	J	K	L	М
Mont	h	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	•	1	2	3	4	5	6	7	8	9	0	Ν	D



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Base Current	I <sub>B</sub>	500	mA
Continuous Collector Current	Ic	3	Α
Peak Pulse Collector Current	I <sub>CM</sub>	6	A

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		1.1 8.8	W mW/°C	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.7 13.6		
Thermal Desistance Junction to Ambient	(Note 5)	Б	113		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	73	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	$R_{ heta JL}$	18.6		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

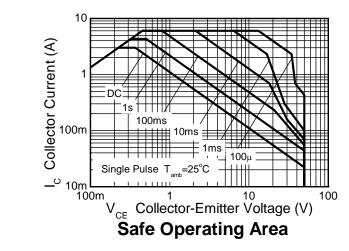
Notes:

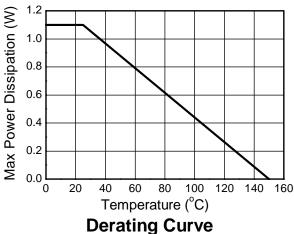
- 5. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is measured at  $t \le 5$  sec.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

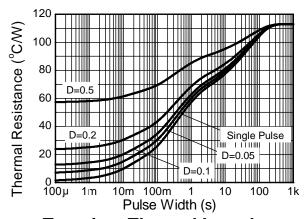
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**







**Transient Thermal Impedance** 



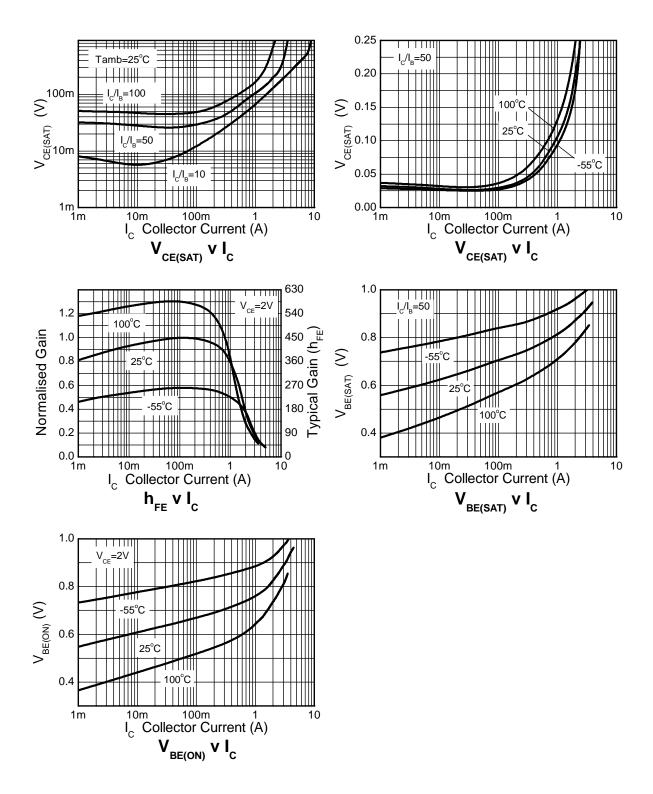
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS	•				•		
Collector-Base Breakdown Voltage		50	190	_	V	$I_C = 100\mu A$	
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	50	65	_	V	$I_C = 10mA$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	8.3	_	V	I <sub>E</sub> = 100μA	
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	100	nA	V <sub>CB</sub> = 40V	
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 4V	
Collector-Emitter Cutoff Current	I <sub>CES</sub>	_	_	100	nA	V <sub>CES</sub> = 40V	
ON CHARACTERISTICS (Note 9)							
		200	400	_		$I_C = 10$ mA, $V_{CE} = 2$ V	
		300	450	_		$I_C = 0.2A, V_{CE} = 2V$	
DC Current Gain	h <sub>FE</sub>	200	400	_	ı	$I_C = 1A$ , $V_{CE} = 2V$	
		100	225	_		I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V	
		_	40	_		I <sub>C</sub> = 6A, V <sub>CE</sub> = 2V	
		_	14	20	mV	I <sub>C</sub> = 0.1A, I <sub>B</sub> = 10mA	
Collector-Emitter Saturation Voltage	.,	_	145	200		I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA	
Collector-Emitter Saturation voltage	V <sub>CE(SAT)</sub>	_	115	200		I <sub>C</sub> = 2A, I <sub>B</sub> = 50mA	
		_	225	300		I <sub>C</sub> = 3A, I <sub>B</sub> = 100mA	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	0.93	1.0	V	I <sub>C</sub> = 3A, I <sub>B</sub> = 100mA	
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>	_	0.88	0.95	V	$I_C = 3A$ , $V_{CE} = 2V$	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f <sub>T</sub>	100	165	_	MHz	$V_{CE} = 10V, I_{C} = 50mA, f = 100MHz$	
Output Capacitance	C <sub>obo</sub>	_	12	20	pF	V <sub>CB</sub> = 10V, f = 1MHz	
Turn-On Time	t <sub>(on)</sub>	_	170	_	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A	
Turn-Off Time		_	750	_	ns	$I_{B1} = I_{B2} = 10 \text{mA}$	

Note: 9. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .



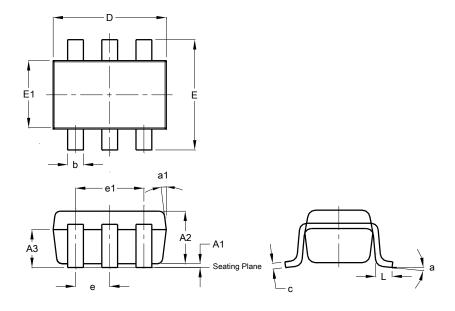
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





## **Package Outline Dimensions**

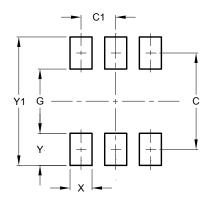
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
А3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All	Dimen	sions	in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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